BF1108; BF1108R

Silicon RF switches

Rev. 04 — 29 May 2008 Product data sheet

1. Product profile

1.1 General description

These switches are a combination of a depletion type Field-Effect Transistor (FET) and a band-switching diode in an SOT143B (BF1108) or SOT143R (BF1108R) package. The low loss and high isolation capabilities of these devices provide excellent RF switching functions. The gate of the MOSFET can be isolated from ground with the diode, resulting in low losses. Integrated diodes between gate and source and between gate and drain protect against excessive input voltage surges.

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Specially designed for low loss RF switching up to 1 GHz

1.3 Applications

- Various RF switching applications such as:
  - Passive loop through for VCR tuner
  - Transceiver switching

1.4 Quick reference data

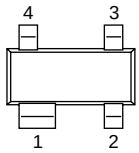
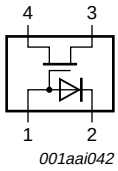
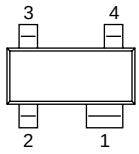
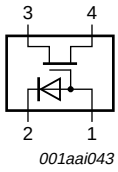
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$L_{ins(on)}$	on-state insertion loss	$R_S = R_L = 50\ \Omega$; $f \leq 1$ GHz; $V_{SK} = V_{DK} = 0$ V; $I_F = 0$ mA	[1]	-	-	2	dB
ISL_{off}	off-state isolation	$R_S = R_L = 50\ \Omega$; $f \leq 1$ GHz; $V_{SK} = V_{DK} = 5$ V; $I_F = 1$ mA		30	-	-	dB
R_{DSon}	drain-source on-state resistance	$V_{KS} = 0$ V; $I_D = 1$ mA		-	12	20	Ω
$V_{GS(p)}$	gate-source pinch-off voltage	$V_{DS} = 1$ V; $I_D = 20\ \mu A$		-	–3	–4	V

[1] I_F = diode forward current.

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BF1108 (SOT143B)				
1	FET gate; diode anode			
2	diode cathode			
3	source	[1]		
4	drain	[1]		
				001aai042
BF1108R (SOT143R)				
1	FET gate; diode anode			
2	diode cathode			
3	source	[1]		
4	drain	[1]		
				001aai043

[1] Drain and source are interchangeable.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BF1108	-	plastic surface-mounted package; 4 leads	SOT143B
BF1108R	-	plastic surface-mounted package; reverse pinning; 4 leads	SOT143R

4. Marking

Table 4. Marking

Type number	Marking code
BF1108	NGp
BF1108R	NHp

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
FET					
V_{DS}	drain-source voltage		-	3	V
V_{SD}	source-drain voltage		-	3	V
V_{DG}	drain-gate voltage		-	7	V
V_{SG}	source-gate voltage		-	7	V
I_D	drain current		-	10	mA
Diode					
V_R	reverse voltage		-	35	V
I_F	forward current		-	100	mA
FET and diode					
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	150	°C

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Typ	Unit
$R_{th(j\text{-}sp)}$	thermal resistance from junction to solder point		[1]	250	K/W

[1] Soldering point of FET gate and diode anode lead.

7. Static characteristics

Table 7. Static characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
FET						
$V_{(BR)GSS}$	gate-source breakdown voltage	V_{DS} = 0 V; I_{GS} = 0.1 mA	7	-	-	V
$V_{GS(p)}$	gate-source pinch-off voltage	V_{DS} = 1 V; I_D = 20 µA	-	–3	–4	V
I_{DSX}	drain cut-off current	V_{GS} = –5 V; V_{DS} = 2 V	-	-	10	µA
I_{GSS}	gate leakage current	V_{GS} = –5 V; V_{DS} = 0 V	-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 0 V; I_D = 1 mA	-	12	20	Ω
Diode						
V_F	forward voltage	I_F = 10 mA	-	-	1	V
I_R	reverse current	V_R = 25 V	-	-	50	nA
		V_R = 20 V; T_{amb} = 75 °C	-	-	1	µA

8. Dynamic characteristics

Table 8. Dynamic characteristics

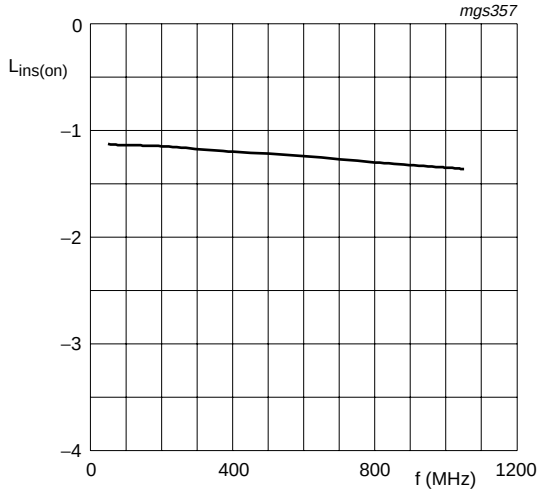
Common cathode; T_{amb} = 25 °C.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
FET and diode							
$L_{ins(on)}$	on-state insertion loss	$V_{SK} = V_{DK} = 0$ V; $I_F = 0$ mA	[1]				
		$R_S = R_L = 50\ \Omega$; f ≤ 1 GHz		-	-	2	dB
		$R_S = R_L = 50\ \Omega$; f = 1 GHz		-	1.3	-	dB
		$R_S = R_L = 75\ \Omega$; f ≤ 1 GHz		-	-	3	dB
ISL_{off}	off-state isolation	$V_{SK} = V_{DK} = 5$ V; $I_F = 1$ mA					
		$R_S = R_L = 50\ \Omega$; f ≤ 1 GHz		30	-	-	dB
		$R_S = R_L = 50\ \Omega$; f = 1 GHz		-	38	-	dB
		$R_S = R_L = 75\ \Omega$; f ≤ 1 GHz		30	-	-	dB
R_{DSon}	drain-source on-state resistance	$V_{KS} = 0$ V; $I_D = 1$ mA		-	12	20	Ω
C_i	input capacitance	f = 1 MHz	[2]				
		$V_{SK} = V_{DK} = 5$ V; $I_F = 1$ mA		-	1	-	pF
		$V_{SK} = V_{DK} = 0$ V; $I_F = 0$ mA		-	0.65	0.9	pF
C_o	output capacitance	f = 1 MHz	[2]				
		$V_{SK} = V_{DK} = 5$ V; $I_F = 1$ mA		-	1	-	pF
		$V_{SK} = V_{DK} = 0$ V; $I_F = 0$ mA		-	0.65	0.9	pF
Diode							
C_d	diode capacitance	f = 1 MHz; $V_R = 0$ V		-	1.1	-	pF
r_D	diode forward resistance	$I_F = 2$ mA; f = 100 MHz	[3]	-	-	0.7	Ω

[1] I_F = diode forward current.

[2] C_i is the series connection of C_{GS} and C_{GK}; C_o is the series connection of C_{GD} and C_{GK}.

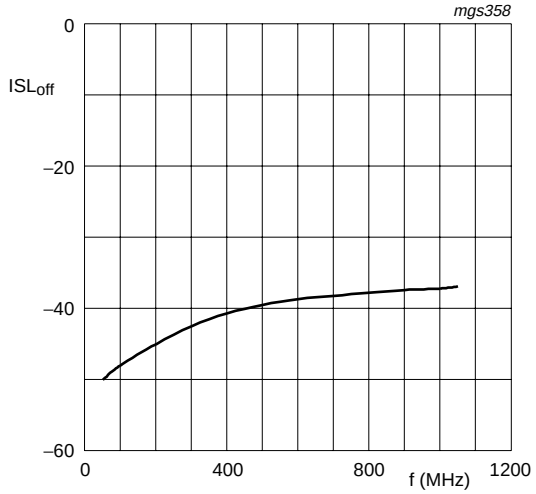
[3] Guaranteed on AQL basis; inspection level S4, AQL 1.0.



$V_{SK} = V_{DK} = 0$ V; $R_S = R_L = 50\ \Omega$; $I_F = 0$ mA (diode forward current).

Measured in test circuit see Figure 3.

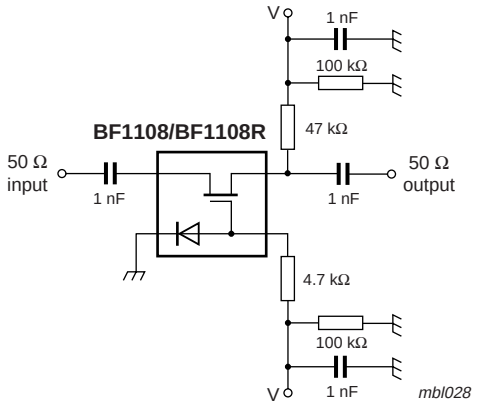
Fig 1. On-state insertion loss as a function of frequency; typical values



$V_{SK} = V_{DK} = 5$ V; $R_S = R_L = 50\ \Omega$; $I_F = 1$ mA (diode forward current).

Measured in test circuit see Figure 3.

Fig 2. Off-state isolation as a function of frequency; typical values



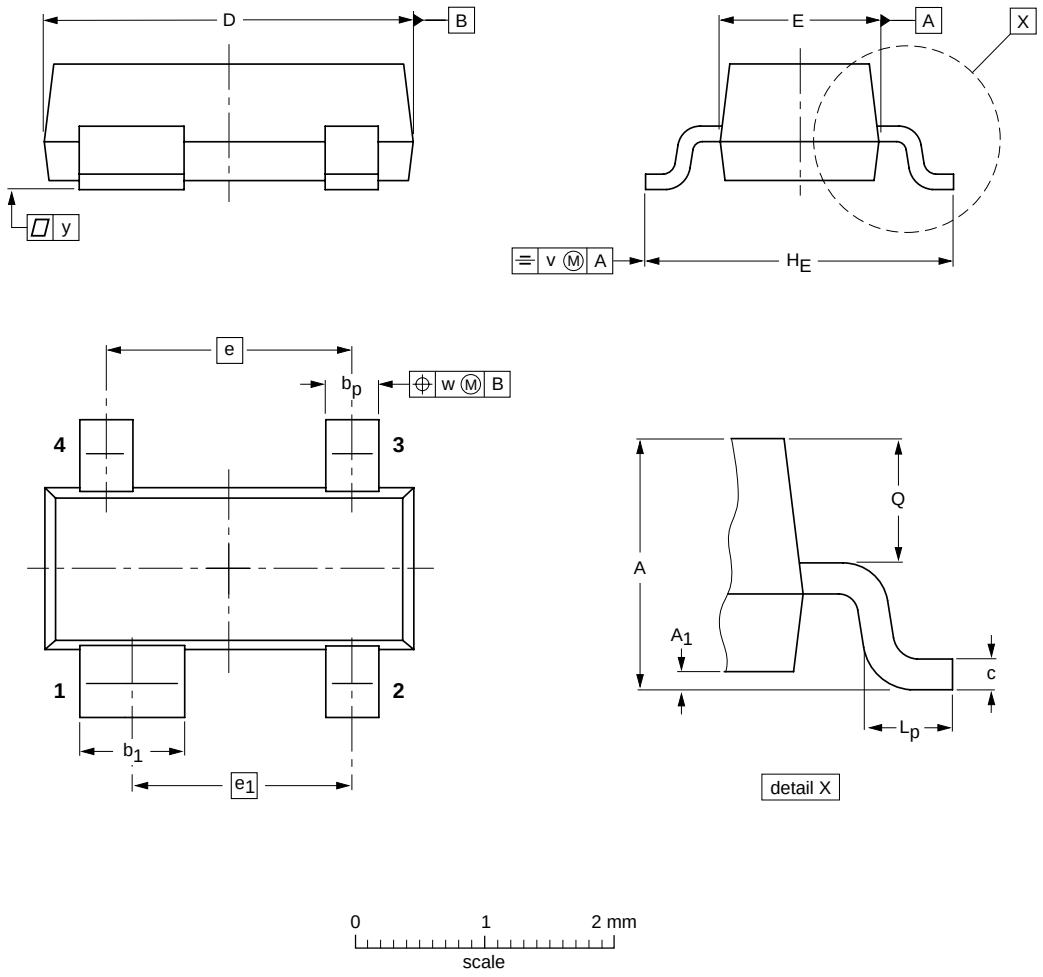
On-state: V = 0 V.

Off-state: V = 5 V.

Fig 3. Test circuit

9. Package outline

Plastic surface-mounted package; 4 leads **SOT143B**



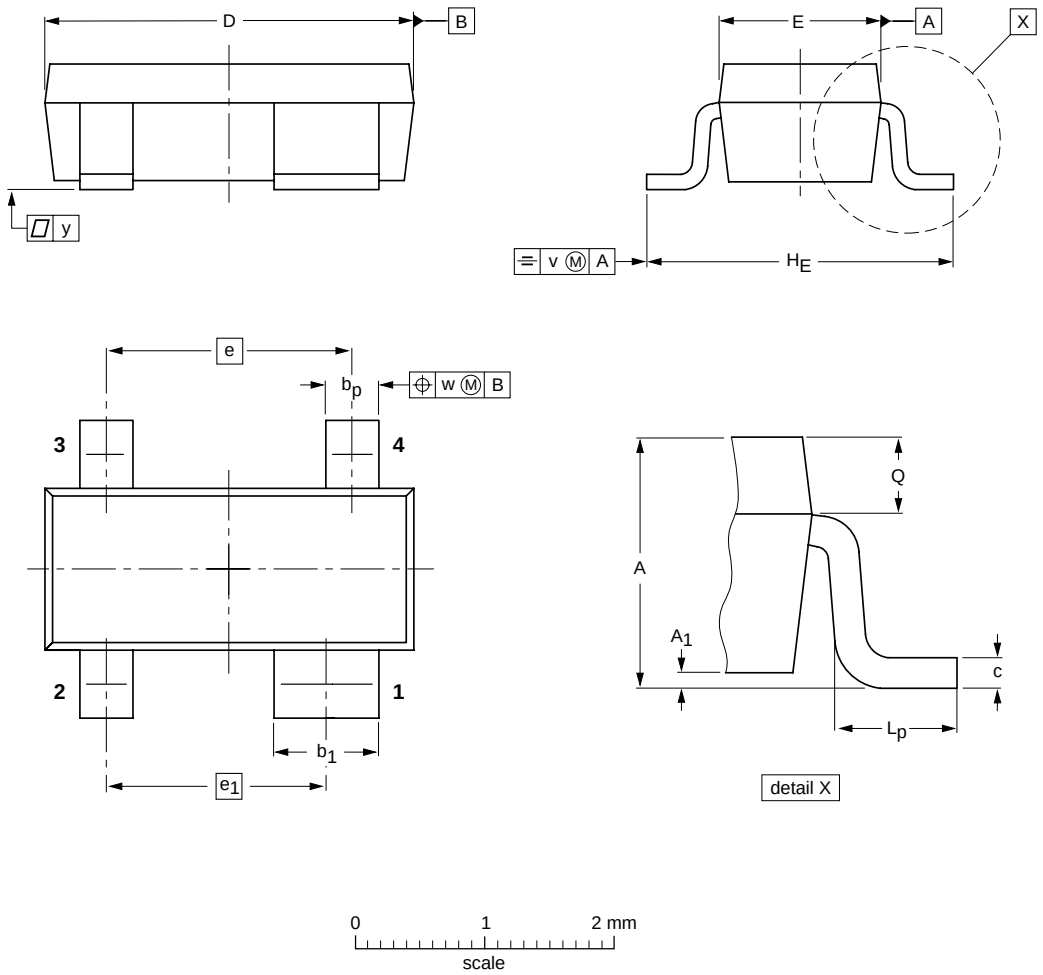
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT143B						~~04-11-16~~ 06-03-16

Fig 4. Package outline SOT143B

Plastic surface-mounted package; reverse pinning; 4 leads **SOT143R**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.55 0.25	0.45 0.25	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT143R			SC-61AA			~~04-11-16~~ 06-03-16

Fig 5. Package outline SOT143R

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
AQL	Acceptable Quality Level
MOSFET	Metal-Oxide Semiconductor Field-Effect Transistor
RF	Radio Frequency
S4	Special inspection level 4
VCR	VideoCassette Recorder

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF1108_BF1108R_4	20080529	Product data sheet	-	BF1108_1108R_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Symbol notation has been adapted to comply with the current guidelines of NXP Semiconductors.			
BF1108_1108R_3 (9397 750 06477)	19991118	Product data sheet	-	BF1108_1108R_2
BF1108_1108R_2 (9397 750 06073)	19990819	Product data sheet	-	BF1108_1108R_1
BF1108_1108R_1 (9397 750 05899)	19990517	Preliminary specification	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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14. Contents

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